

IN THE CLAIMS:

1. (Currently Amended) A data memory circuit, comprising:
 - a plurality of addressable memory cells;
 - a command-decoding device configured for decoding external commands received from a source external to the data memory circuit;
 - a control device configured for controlling and initiating operations on the memory cells in response to the decoded external commands; and
 - a command buffer device configured for buffer-storing an external command received in a critical operating state period during which execution of the external command is impermissible and for releasing the buffer-stored external command for execution after end of the critical operating state period, wherein the command buffer device receives from the control device a multi-bit status signal which indicates the critical operating state period and a ~~type of~~ critical operating state selected from one of a plurality of critical operating states, wherein the selected critical operating state is determined by activation of multiple bits of the multi-bit status signal.
2. (Currently Amended) The data memory circuit of claim 1, wherein:
 - a plurality of critical operating states are possible, and in one or more critical operating states, a set of commands is impermissible; and
 - the command buffer device includes a buffer circuit assigned to each individual command of the decoded set of impermissible external commands.
3. (Previously Presented) The data memory circuit of claim 2, wherein each buffer circuit comprises:
 - a state evaluation circuit, responsive to the multi-bit status signal, for generating a buffer standby signal during at least one operating state that is critical for the execution of respective impermissible command; and
 - a logic circuit for setting a bi-stable element into a first state when the assigned command appears while the buffer standby signal is active and for re-generating the assigned command after the buffer standby signal has ended.

4. (Currently Amended) The data memory circuit of claim 3, wherein the command decoding device comprises:

a predecoder, which, for each received command, activates a command line assigned to the received command; and

an end decoder which excites selected enable lines of the control device depending on which of the command lines is activated; and wherein each buffer circuit is connected to a respectively assigned command line between the predecoder and the end decoder to receive the command from the respective command line and to apply a re-generated command generated to the respective command line.

5. (Previously Presented) The data memory circuit of claim 4, wherein each buffer circuit includes a switch in a path of the respective command line, wherein the switch is opened precisely while a buffer standby signal is active to inhibit forwarding of an activation of the command line effected by the predecoder to the end decoder.

6. (Currently Amended) The data memory circuit of claim 5, wherein [[a]] the source of external commands is adapted to a specification of the data memory circuit with regard to command-issuing times, and wherein the command buffer device handles external commands whose execution leads to termination of internally controlled processes in the data memory circuit.

7. (Original) The data memory circuit of claim 6, wherein the command buffer device handles external commands whose execution leads to termination of a self-controlled data-refresh process in the memory circuit.

8. (Original) The data memory circuit of claim 1, wherein the control device includes blockage elements for blocking execution of commands during the critical operating state period, and wherein the command buffer device directly forwards commands received during the critical operating state period.

9. (Original) The data memory circuit of claim 1, wherein the command buffer device inhibits forwarding of the received command to the control device during the critical operating state period.

10. (Currently Amended) A data memory circuit, comprising:
a plurality of addressable memory cells;
a command decoder configured for receiving external commands from a source external to the data memory circuit, the command decoder having a plurality of command-buffer circuits for buffer-storing external commands received during critical operation state periods when execution of the commands is impermissible and for releasing the buffer-stored external commands for execution after the critical operation state periods, wherein each command-buffer circuit receives a multi-bit status signal which indicates the critical operating state period and a ~~type of~~ critical operating state selected from one of a plurality of critical operating states, wherein the selected critical operating state is determined by activation of multiple bits of the multi-bit status signal; and
an internal controller configured for controlling operations on the memory cells in response to external commands from the command decoder.
11. (Original) The data memory circuit of claim 10, wherein the command decoder further comprises:
a predecoder;
an end decoder; and
a plurality of command lines connecting the plurality of command-buffer circuits between the predecoder and the end decoder, wherein the predecoder assigns and activates one or more command lines in response to the received commands and the end decoder excites one or more enable lines of the internal controller corresponding to the activated command lines.
12. (Currently Amended) The data memory circuit of claim 11, wherein each command-buffer circuit comprises:
a state evaluation circuit configured for generating a buffer standby signal during the critical operation state periods; and
a logic circuit configured for holding an assigned command while the buffer standby signal is active and for forwarding the assigned command to the end decoder after the buffer standby signal has ended.

13. (Original) The data memory circuit of claim 12, wherein each command-buffer circuit further comprises a switch disposed in-line with the respective command line connecting the predecoder and the end decoder, wherein the switch is connected to the state evaluation circuit and opens when the buffer standby signal is active.

14. (Original) The data memory circuit of claim 12, wherein the internal controller includes a command-blocking circuit for blocking execution of commands during the critical operation state periods.

15. (Original) The data memory circuit of claim 12, wherein the command buffer circuits handle external commands whose execution leads to termination of internally controlled processes in the data memory circuit.

16. (Original) The data memory circuit of claim 12, wherein the command buffer circuits handle external commands whose execution leads to termination of a self-controlled data-refresh process in the memory circuit.

17. (Currently Amended) A data memory circuit, comprising:

a plurality of addressable memory cells;

a decoder means for receiving and decoding commands, the decoder means having a plurality of command-buffer means for buffer-storing commands received during critical operation state periods when execution of the commands is impermissible and for releasing the buffer-stored commands for execution after respective critical operation state periods, wherein each command-buffer means receives a multi-bit status signal which indicates the critical operating state periods and a critical operating state selected from one of a plurality of critical operating states, wherein the selected critical operating state is determined by activation of multiple bits of the multi-bit status signal; and

a controller means for controlling operations on the memory cells in response to commands from the decoder means and for providing the multi-bit status signal to the command-buffer means.

18. (Original) The data memory circuit of claim 17, wherein the decoder means further comprises a plurality of command lines connecting the plurality of command-buffer means between a predecoder means for assigning and activating one or more command lines in response to the received commands and an end decoder means for activating one or more enable lines of the controller means corresponding to the activated command lines.

19. (Original) The data memory circuit of claim 18, wherein each command-buffer means comprises:

a state evaluation means for evaluating an operating state of the memory cells and for generating a buffer standby signal during the critical operation state periods; and

a logic circuit means for holding an assigned command while the buffer standby signal is active and for forwarding the assigned command to the end decoder after the buffer standby signal has ended.

20. (Original) The data memory circuit of claim 19, wherein each command-buffer means further comprises a switching means for selectively opening and closing the respective command line, the switching means disposed in-line with the respective command line connecting the predecoder means and the end decoder means, wherein the switching means is connected to the state evaluation circuit and opens when the buffer standby signal is active.

21. (Currently Amended) A method for controlling the execution of commands in a memory device comprising a plurality of addressable memory cells, the method comprising:

receiving and analyzing a multi-bit status indication signal which identifies a critical operating state selected from a plurality of critical operating states that is not compatible with the execution of an external command, wherein the multi-bit status indication signal is provided by an internal control device of the memory device to a command decoder of the memory device, wherein the selected critical operating state is determined by activation of multiple bits of the multi-bit status signal;

receiving the external command while the memory device is performing a critical operation in the selected critical operating state making execution of the external command impermissible;

buffering the external command until the memory device completes the critical operation; and then

executing the external command.

22. (Currently Amended) A data memory circuit, comprising:

a plurality of addressable memory cells;

a command-decoding device configured for decoding external commands received from a source external to the data memory circuit;

a control device configured for controlling and initiating operations on the memory cells in response to the decoded external commands; and

a command buffer device configured for buffer-storing an external command received in a critical operating state period during which execution of the external command is impermissible and for releasing the buffer-stored external command for execution after end of the critical operating state period, said command-buffer device containing comprising a state evaluation circuit configured for:

receiving and analyzing a multi-bit status indication signal from the control device to ~~identify one or more~~ indicative of a critical operating state[[s]] selected from a plurality of critical operating states which are not compatible with execution of the external command, wherein the selected critical operating state is determined by activation of multiple bits of the multi-bit status signal.